修订记录' -' ' . /01.2'3.4532' '

A	2022.4.7		JSCJ-DTC123JKA+JSCJ-DTA123JKA+LRC-LMUN5335DW1T1G		

描述''-''(.1430C>05?1'

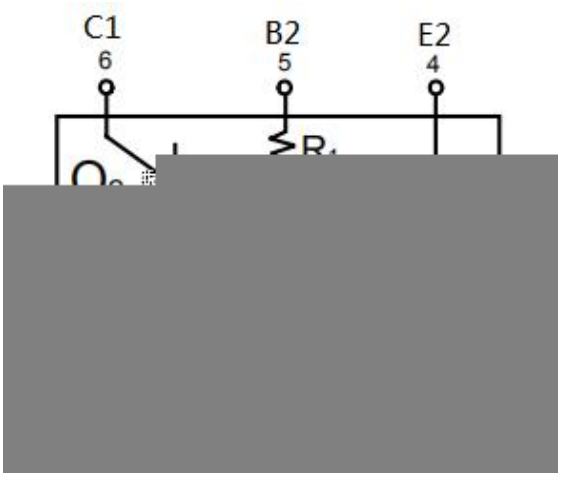
silicon NPN and PNP transistor in a SOT-363 Plastic Package

特征''-''9.<>D3.1'

With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process, HF Product.

用途''-'')CC;04<>05?1''

Switching applications, interface circuit and driver circuit applications.



放大及印章代码''-''89,':;<1104<>05?1'@' <3A0?B'

Marking	H335

'

Parameter	Symbol	Rating	Unit
Supply Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	12	V
		-5	V
Output Current	I_O	100	mA
Collector Dissipation	P_C	187	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55～150	

'

Parameter Symbol

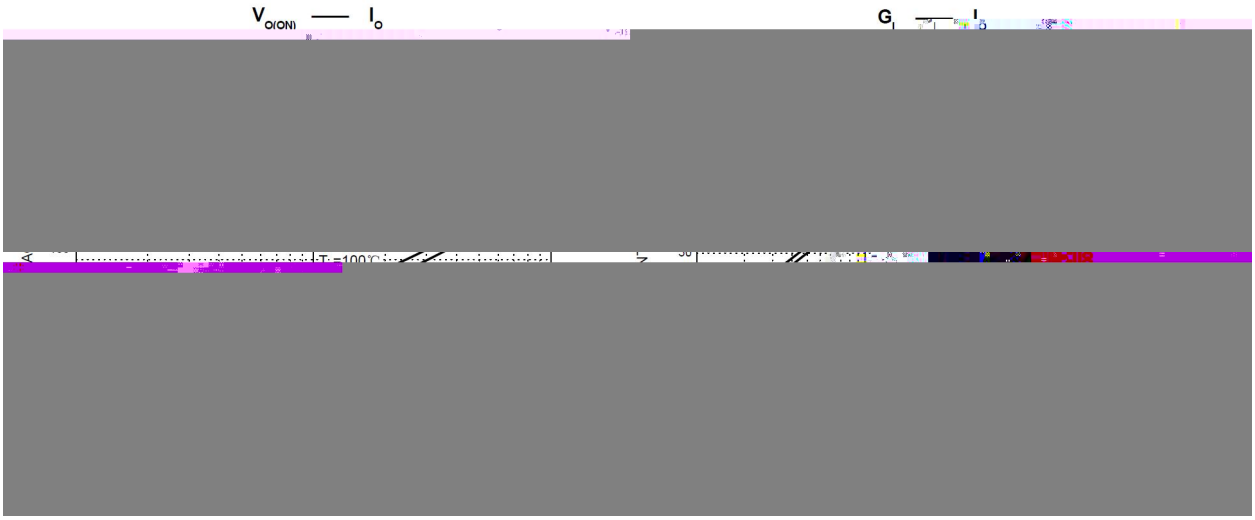
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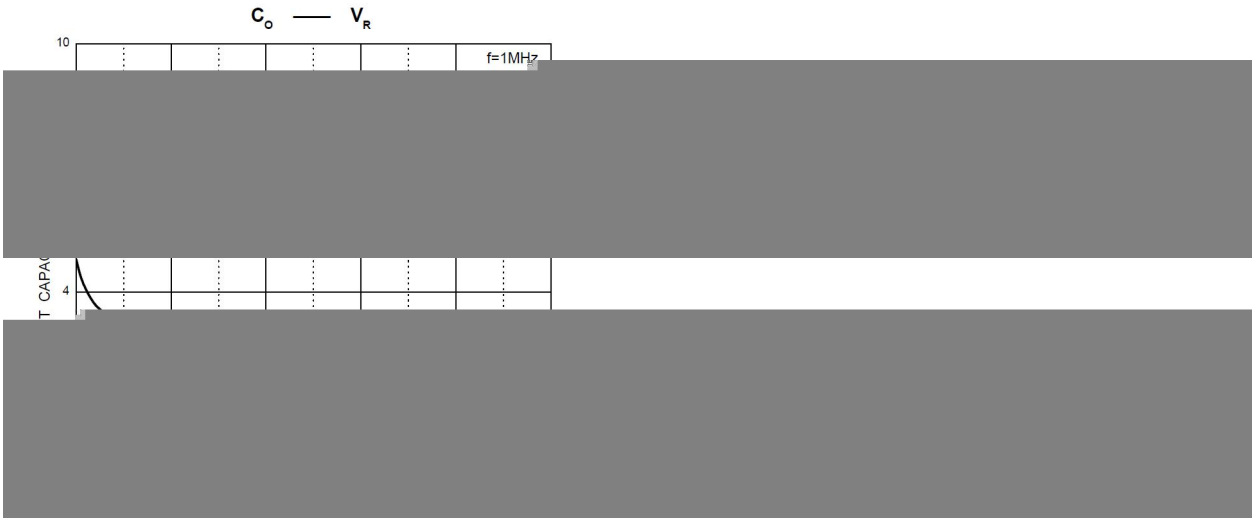
Parameter	Symbol	Rating	Unit
Supply Voltage	V_{CC}	-50	V
Input Voltage	V_{IN}	-12	V
		5	V
	I_O	-100	mA

er Dissi ضذ

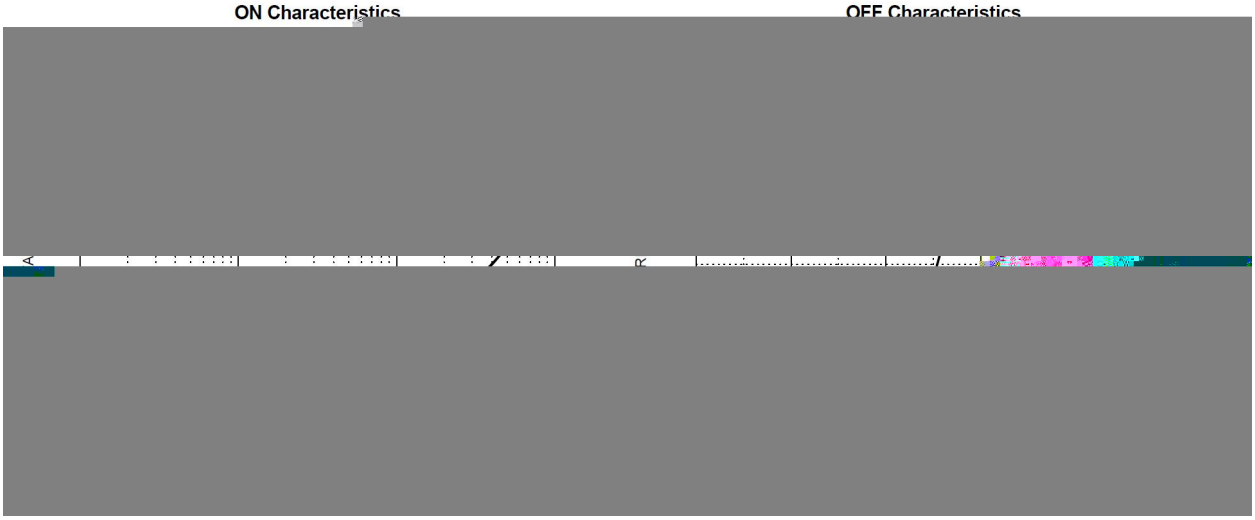
电参数曲线图' ' -' ' , ; . 4>304<;' : 8<3<4>. 301>04' : D3 / . J " K " N'



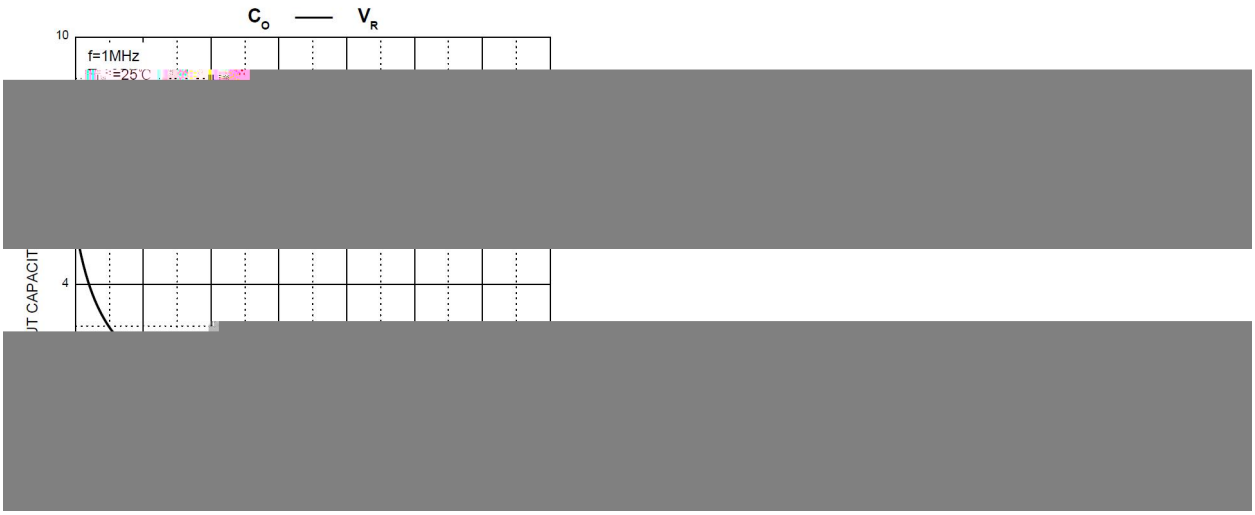




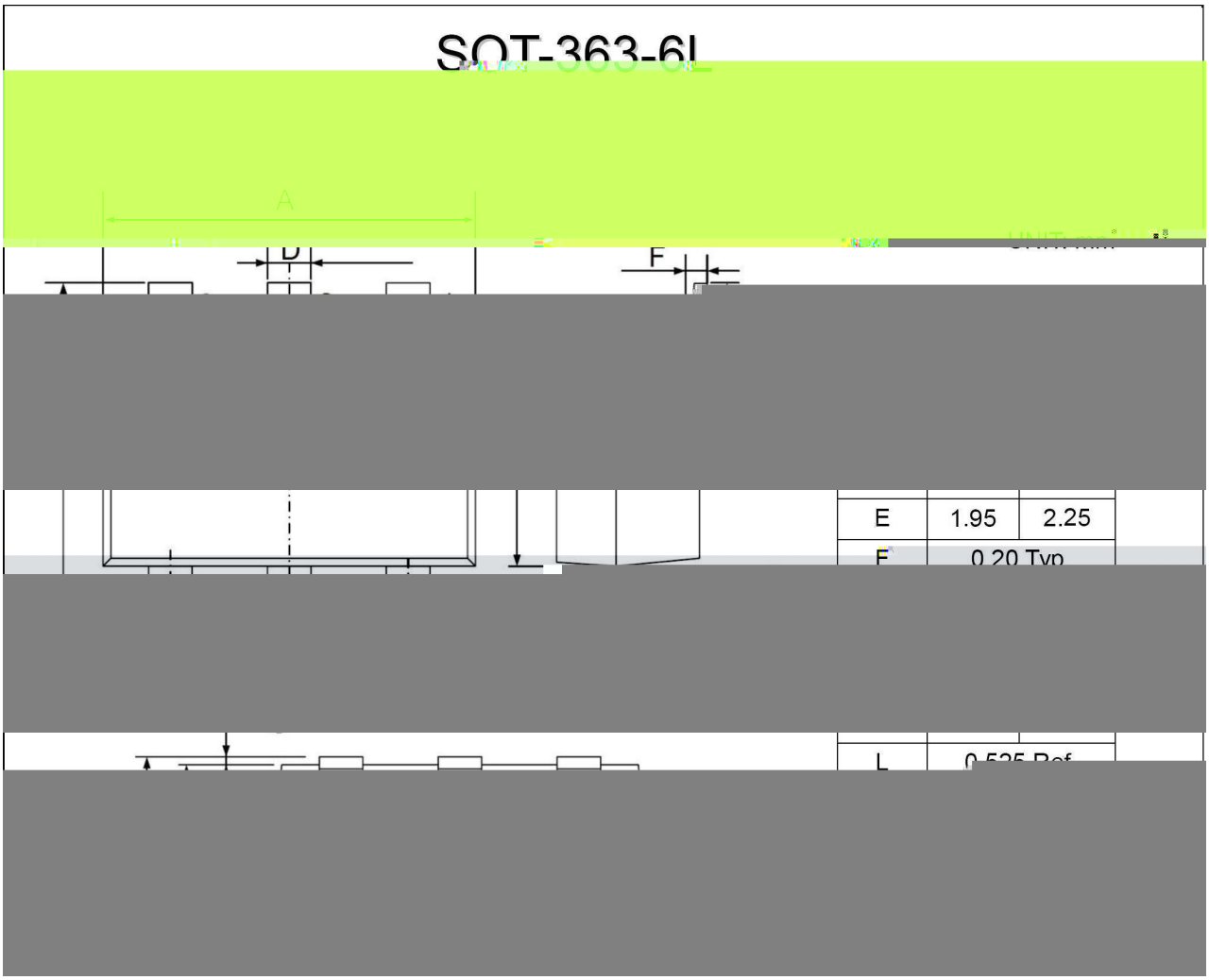
电参数曲线图' ' -' ' , ; . 4>304<;' : 8<3<4>. 301>04' : D3 / . JK " KN'







外形尺寸图' ' -' ' K<4A<B.' (0 I .?105?1'



回流焊温度曲线图J无铅N' '-' ' T mp ratur Pr fil f r IR R fl w S l rin (Pb-Fr)



				Note:
1	150 180	60 90sec;		1.Preheating:150~180 , Time:60~90sec.
2	245 5	5 0.5sec;		